

# Pressure dependence of Raman phonons of Ge and $3C-S$

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Pressure dependence of the linewidth of the soft phonons in PbTiO <sub>3</sub> . Solid State Communications, 1983, 48, 221-224.	1.9	31
2	High-pressure Raman study of zone-center phonons in PbTiO <sub>3</sub> . Physical Review B, 1983, 28, 7260-7268.	3.2	231
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111	Evidence for the $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"} \langle \text{mml:mi mathvariant="bold"} \rangle R \langle \text{mml:mi} \rangle \langle \text{mml:mn} \rangle 8 \langle \text{mml:mn} \rangle \langle \text{mml:math} \rangle$ Phase of Germanium. <i>Physical Review Letters</i> , 2013, 110, 085502.	7.8	27
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163	Silicon carbide (SiC) mode Gr <sup>1/4</sup> neisen parameters. , 0, , 1-6.		0
164	Germanium (Ge), phonon dispersion, phonon frequencies. , 0, , 1-6.		0

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166	Germanium (Ge), data from Raman measurements. , 0, , 1-6.		0
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